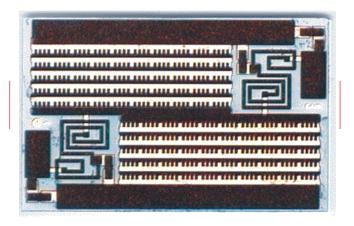
# Keysight Technologies

# 6 GHz Integrated GaAs Diode Limiter 1GG5-4028



Data Sheet

#### Features

- High forward voltage:4.1V Typ. @ 1 mA
- Good port match:
   S11 < -18 dB typ.</li>
   S22 < -18 dB typ.</li>
- Low insertion loss:<0.5 dB typ. @ 3 GHz</li><0.8 dB typ. @ 6 GHz</li>
- P-1dB: 26 dBm typ.
- Distortion:

SHI: +100 dBm typ.

THI: +53 dBm typ.

TOI: +50 dBm typ.



# Description

The 1GG5-4028 is a 6 GHz reverse power protection (RPP) and limiter GaAs ID. The device can be used to protect sensitive RF circuits from excess RF power, DC transients and ESD from DC to 6 GHz. The circuit contains planar–doped–barrier (PDB) diodes with integrated matching networks consisting of spiral inductors and MIM capacitors. The device is fabricated with the modified barrier integrated diode (MBID) process. This process allows the barrier height of the diodes and the number of diodes in each "stack" to be optimized for low harmonic distortion when P in < 20 dBm while limiting transmitted power to less than 1 watt when  $P_{\rm in}$  = 10 watts.

#### Absolute maximum ratings<sup>1</sup>

(@ T, = 25 °C, unless otherwise indicated)

Symbol	Parameters/conditions	Min	Max	Units
P <sub>cont</sub>	Maximum continuous RF input power		5 (37)	Watts (dBm)
cont	Maximum continuous DC current		160	mA
$T_j$	Junction temperature		150	°C
Тор	Operating temperature	-55	100	°C
T <sub>st</sub>	Storage temperature	-65	+165	°C
T <sub>max</sub>	Max. assembly temperature		300	°C

<sup>1.</sup> Operation in excess of any one of these conditions may result in permanent damage to this device.  $T_A = 25^{\circ}\text{C}$  except for  $T_{ch}$ ,  $T_{stg}$ , and  $T_{max}$ .

# **Applications**

The 1GG5-4028 was designed for reverse power protection (RPP), limiter and ESD protection applications. When used as a shunt limiter, 1 dB compression occurs when  $P_{\rm in} = \sim 25$  dBm and small-signal insertion loss is less than 1 dB up to 6 GHz. The 1GG5-4028 can also protect sensitive components from ESD damage. The degree of protection offered is dependent on the protected component's characteristics. ESD damage level for the 1GG5-4028 by itself is greater than 8 kv (measured with IEC801–2, 150 pF, 330 ohm ESD generator).

# Biasing and operation

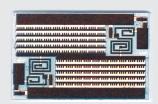
The 1GG5-4028 needs no bias.

# Assembly techniques

Epoxy die-attach using conductive epoxy or solder die-attach using a fluxless AuSu solder preform can be used for assembly. Gold thermosonic wedge bonding with 0.7 mil diameter Au wire is recommended for all bonds. Tool force should be  $22 \pm 1$  gram, stage temperature should be  $150 \pm 2^{\circ}\text{C}$ , and ultrasonic power and duration should be  $64 \pm 1$  dB and  $76 \pm 8$  msec, respectively. The bonding pad and chip backside metallization is gold.

Diodes are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly. Diode ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful diode performance and reliability.

Keysight document, "GaAs MMIC ESD, Die Attach and Bonding Guidelines - Application Note" (5991–3484EN) provides basic information on these subjects.



- Chip size: 1310′860 mm (51.6′33.7 mils)
- Chip size tolerance: ± 10 mm (± 0.4 mils)
- Chip thickness:  $127 \pm 15$  mm  $(5.0 \pm 0.6 \text{ mils})$
- RF pad dimensions: 175′80 mm (6.9′ 3.1 mils), or larger

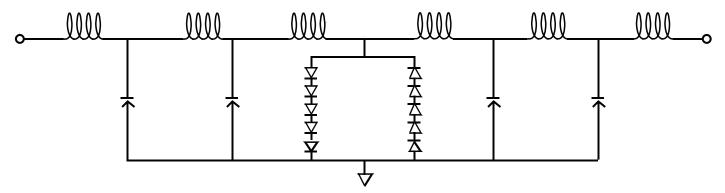
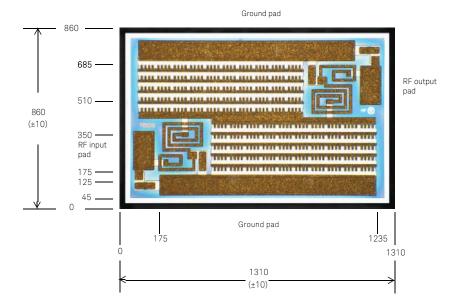


Figure 1. 1GG5-4028 schematic



- I. All dimensions in microns.
- 2. RF pad dim.: 175′80 mm.
- 3. All other dimensions: ± 5 mm (unless otherwise noted).
- Chip thickness: 127 ± 15 mm.

Figure 2. 1GG5-4028 bond pad locations

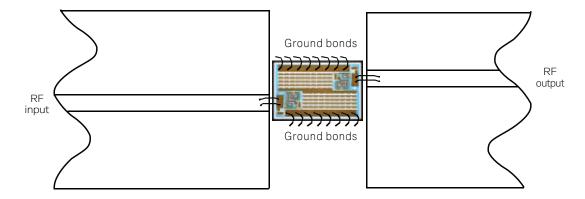


Figure 3. 1GG5-4028 assembly diagram

#### (Input and output bond wire inductance = 0.3 nH)

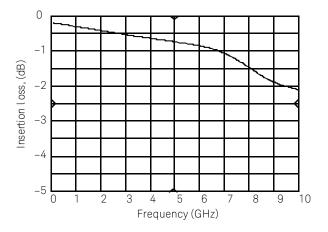


Figure 4. Typical insertion loss vs. frequency

### (Input and output bond wire inductance = 0.3 nH)

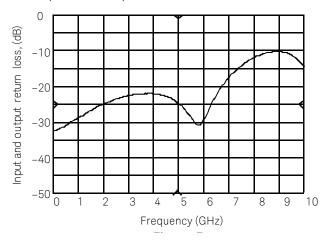


Figure 5. Typical input and output return loss vs. frequency

# Typical S-parameters

 $(T_{chuck} = 25 \, ^{\circ}\text{C}, \text{ input and output bond wire inductance} = 0.3 \, \text{nH})$ 

Freq (GHz)	S11,S 22			S21,		
	dB	Mag	Ang	dB	Mag	Ang
0.05	-32.221	0.024	-2.241	-0.228	0.974	-1.459
0.10	-32.144	0.025	-4.121	-0.227	0.974	-2.888
0.5	-30.746	0.029	-26.764	-0.263	0.970	-14.254
1.0	-28.664	0.037	-57.231	-0.322	0.964	-28.226
1.5	-26.618	0.047	-83.770	-0.373	0.958	-42.135
2.0	-24.730	0.058	-108.166	-0.436	0.951	-56.078
2.5	-23.303	0.068	-129.362	-0.490	0.945	-70.058
3.0	-22.260	0.077	-148.565	-0.548	0.939	-84.101
3.5	-21.710	0.082	-165.969	-0.606	0.933	-98.320
4.0	-21.662	0.083	178.983	-0.652	0.928	-112.776
4.5	-22.273	0.077	165.600	-0.707	0.922	-127.450
5.0	-24.141	0.062	156.143	-0.757	0.917	-142.440
5.5	-27.835	0.041	160.793	-0.798	0.912	-157.782
6.0	-28.899	0.036	-146.270	-0.874	0.904	-175.401
6.5	-22.176	0.078	-126.263	-0.961	0.895	168.026
7.0	-17.240	0.137	-132.438	-1.093	0.882	150.845
7.5	-13.903	0.202	-144.972	-1.271	0.864	133.106
8.0	-11.640	0.262	-159.638	-1.495	0.842	114.903
8.5	-10.318	0.305	-174.971	-1.720	0.820	96.133
9.0	-9.959	0.318	169.854	-1.910	0.803	76.497
9.5	-10.953	0.283	156.718	-2.028	0.792	55.121
10.0	-14.404	0.190	156.832	-2.155	0.780	30.458

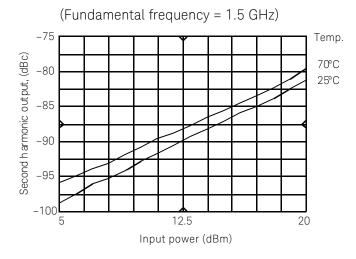


Figure 6. Typical second harmonic performance vs. temperature

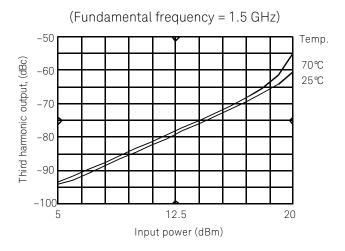


Figure 7. Typical third harmonic performance vs. temperature

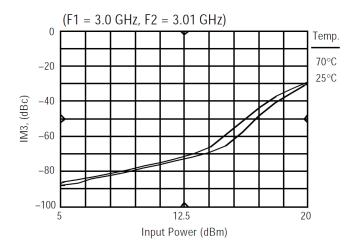


Figure 8. Typical third order intermodulation vs. temperature

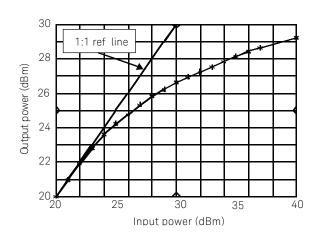


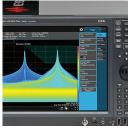
Figure 9. Typical P<sub>out</sub> vs. P<sub>in</sub>

- 1. All data measured on individual devices mounted in test package
- 2.  $\bigcirc$  T<sub>A</sub> = 25 °C (except where noted).
- This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications.

# Evolving

Our unique combination of hardware, software, support, and people can help you reach your next breakthrough. We are unlocking the future of technology.







From Hewlett-Packard to Agilent to Keysight

myKeysight

myKeysight

www.keysight.com/find/mykeysight

A personalized view into the information most relevant to you.

KEYSIGHT SERVICES
Accelerate Technology Adoption.
Lower costs.

**Keysight Services** 

www.keysight.com/find/service

Keysight Services can help from acquisition to renewal across your instrument's lifecycle. Our comprehensive service offerings—one-stop calibration, repair, asset management, technology refresh, consulting, training and more—helps you improve product quality and lower costs.

#### Keysight Channel Partners

#### www.keysight.com/find/channelpartners

Get the best of both worlds: Keysight's measurement expertise and product breadth, combined with channel partner convenience.

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifi cations. Customers considering the use of this, or other Keysight Technologies GaAs ICs, for their design should obtain the current production specifications from Keysight. In this data sheet the term typical refers to the 50th percentile performance. For additional information contact Keysight at MMIC\_Helpline@keysight.com.

www.keysight.com/find/mmic

For more information on Keysight Technologies' products, applications or services, please contact your local Keysight office. The complete list is available at: www.keysight.com/find/contactus

Americas

Canada (877) 894 4414 Brazil 55 11 3351 7010 Mexico 001 800 254 2440 United States (800) 829 4444

Asia Pacific

Australia 1 800 629 485 800 810 0189 China Hong Kong 800 938 693 1 800 11 2626 India Japan 0120 (421) 345 Korea 080 769 0800 Malaysia 1 800 888 848 Singapore 1 800 375 8100 Taiwan 0800 047 866 Other AP Countries (65) 6375 8100

#### Europe & Middle East

For other unlisted countries: www.keysight.com/find/contactus (BP-06-08-16)

Opt. 3 (IT)

0800 0260637



United Kingdom

www.keysight.com/go/quality Keysight Technologies, Inc. DEKRA Certified ISO 9001:2015 Quality Management System

